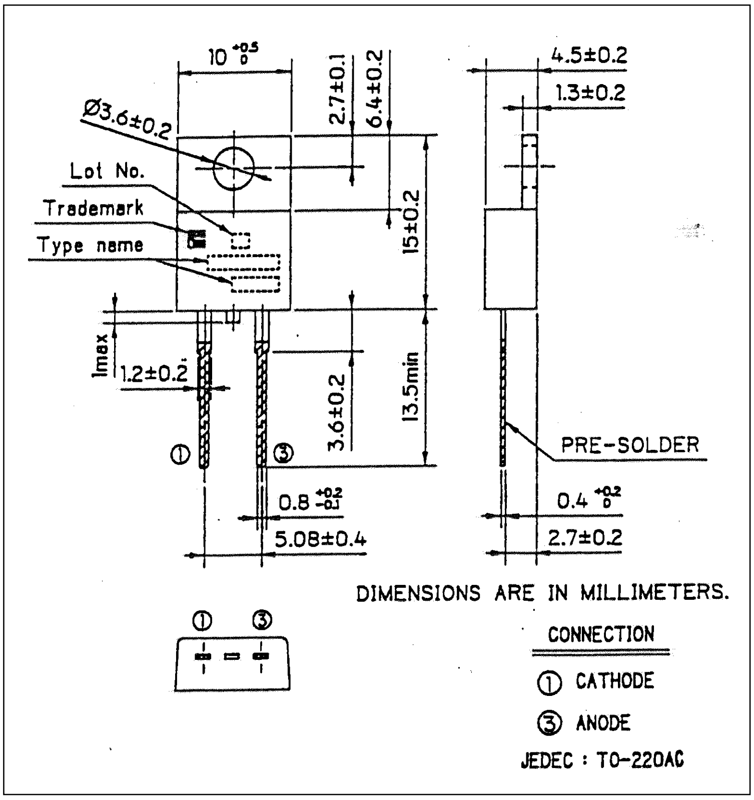
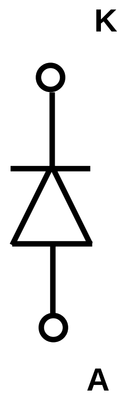
ERW10-120(10A/1200V)

Fast Recovery Diode for IGBT

Outline Drawings **Units mm**



Equivalent circuit



Maximum ratings and characteristics

Absolute maximum ratings (Tc=25°C)

Item	Symbol	Test Conditions		Ratings	Units
Repetitive Reverse Voltage	V_{RRM}			1200	V
Repetitive peak surge current	I_{FM}	20kHz Duty 50% Squ. wave	Tc=123°C	10	A
			Tc=25°C	32	A
Average rectiffied forward current	$I_{F(A)}$	DC		10	A
Non-repetitive peak surge current	I_{FSM}	Pulse 10ms, sin. wave		85	A
Maximam Power Dissipaion	Po			60	W
Operating Temperature	Tj			+150	℃
Storage Temperature	Tstg			-40 to +150	℃
Mounting Screw Torque				50	N·cm

Electrical characteristics (at Tc=25°C unless otherwise specified)

Item	Symbol	Test Conditions	Max	Units
Reverse Current	I_R	V_R = 1200V	1.0	mA
Foward voltage	V_{FM}	I_F = 10A	3.0	V
Reverse recovery time	trr	I_F = 10A,VR=200V, di/dt=100A/µs	0.3	µs

Thermal resistance characteristics

Item	Symbol	Test Conditions	Max	Units
Thermal resistance	$R_{th(j-c)}$	junction to case	2.08	°C/W

■ Characteristics